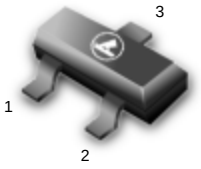
Dual Serise Switching Diodes

LDAN202KLT1G
S-LDAN202KLT1G

FEATURES

- Ultra high speed switching
- Suitable for high packing density layout.
- High reliability.
- We declare that the material of product is ROHS compliant.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



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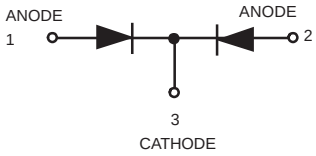

DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LDAN202KLT1G S-LDAN202KLT1G	N	3000/Tape&Reel
LDAN202KLT3G S- LDAN202KLT3G	N	10000/Tape&Reel

MAXIMUM RATINGS (Each Diode)

Rating	Symbol	Value	Unit
Reverse Voltag	V_R	80	Vdc
Forward Current	I_o	100	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	300	mAdc
Forward voltage(If = 100mA)	V_F	1.2	V
Reverse current (Vr = 70V)	I_R	0.1	uA
Capacitance between terminals(f =1MHz)	C_T	3.5	pF
Reverse recovery time(Vr= 6V,If=5 mA)	Trr	4	nS

ELECTRICAL CHARACTERISTIC CURVES

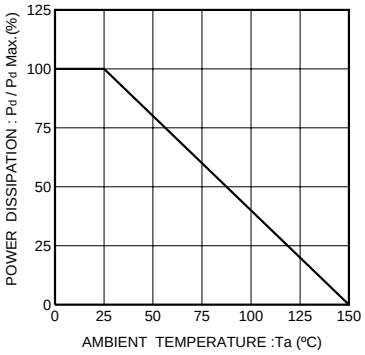

Fig.1 Power attenuation curve

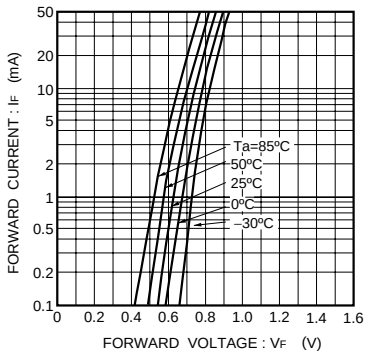

Fig.2 Forward characteristics

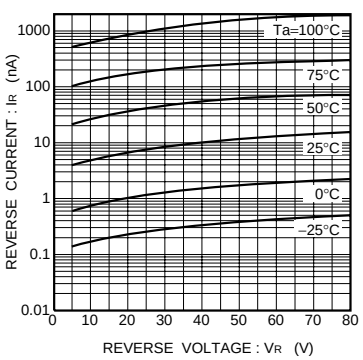

Fig.3 Reverse characteristics

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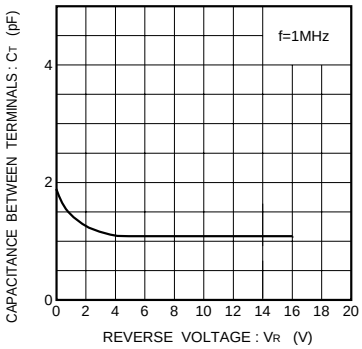

Fig.4 Capacitance between terminals characteristics

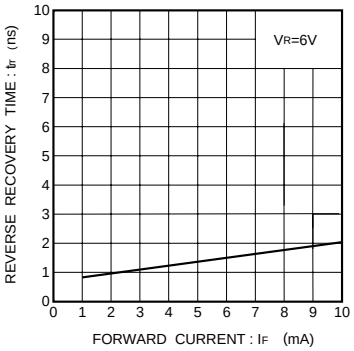

Fig.5 Reverse recovery time

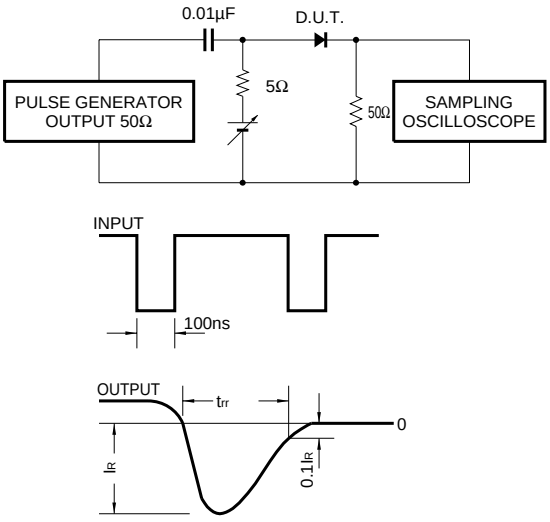

Fig.6 Reverse recovery time (t_{rr}) measurement circuit

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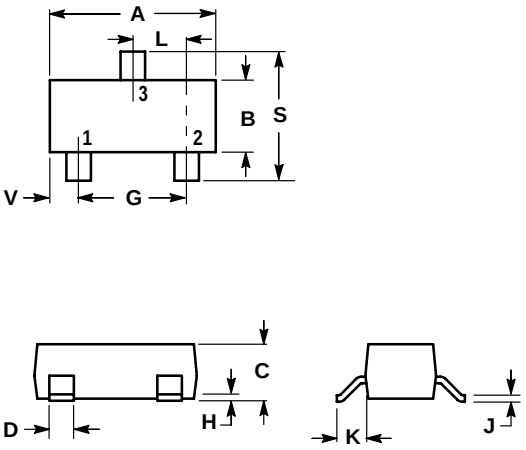

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60